

January 2015

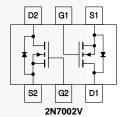
# 2N7002V / 2N7002VA N-Channel Enhancement Mode Field Effect Transistor

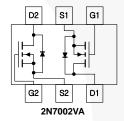
#### **Features**

- Dual N-Channel MOSFET
- · Low On-Resistance
- · Low Gate Threshold Voltage
- · Low Input Capacitance
- · Fast Switching Speed
- · Low Input/Output Leakage
- · Ultra-Small Surface Mount Package
- · Lead Free by Design/RoHS Compliant



**SOT -563F**\* Pin1 and Pin4 are exchangeable.





# **Ordering Information**

| Part Number | Top Mark | Package                   | Packing Method |  |
|-------------|----------|---------------------------|----------------|--|
| 2N7002V     | AB       | SOT-563F 6L Tape and Reel |                |  |
| 2N7002VA    | AC       | SOT-563F 6L Tape and Reel |                |  |

# **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at  $T_A = 25$ °C unless otherwise noted.

| Symbol                            | Parameter                                     |            | Value       | Unit |
|-----------------------------------|-----------------------------------------------|------------|-------------|------|
| V <sub>DSS</sub>                  | Drain-Source Voltage                          |            | 60          | V    |
| V <sub>DGR</sub>                  | Drain-Gate Voltage (R <sub>GS</sub> ≤ 1.0 MΩ) |            | 60          | V    |
| V <sub>GSS</sub>                  | Gate-Source Voltage                           | Continuous | ±20         | V    |
|                                   |                                               | Pulsed     | ±40         |      |
| I <sub>D</sub> D                  | Drain Current                                 | Continuous | 280         | mA   |
|                                   |                                               | Pulsed     | 1.5         | Α    |
| T <sub>J</sub> , T <sub>STG</sub> | Junction and Storage Temperature Range        |            | -55 to +150 | °C   |

#### **Thermal Characteristics**

Values are at T<sub>A</sub> = 25°C unless otherwise noted.

| Symbol          | Parameter                                              | Value | Unit  |
|-----------------|--------------------------------------------------------|-------|-------|
| В               | Total Device Dissipation                               | 250   | mW    |
| P <sub>D</sub>  | Derate Above T <sub>A</sub> = 25°C                     | 2.0   | mW/°C |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient <sup>(1)</sup> | 500   | °C/W  |

#### Note:

1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch. Minimum land pad size.

# **Electrical Characteristics**

Values are at  $T_A$  = 25°C unless otherwise noted.

| Symbol              | Parameter                         | Conditions                                                                | Min. | Тур.  | Max. | Unit |
|---------------------|-----------------------------------|---------------------------------------------------------------------------|------|-------|------|------|
| Off Charact         | eristics <sup>(2)</sup>           |                                                                           |      | •     |      |      |
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage    | $V_{GS} = 0 \text{ V}, I_D = 10 \mu\text{A}$                              | 60   | 78    |      | V    |
| I <sub>DSS</sub>    | Zero Gate Voltage Drain Current   | V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V                             |      | 0.001 | 1.0  | μА   |
|                     |                                   | V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V,<br>T <sub>J</sub> = 125°C  |      | 7     | 500  |      |
| I <sub>GSS</sub>    | Gate-Body Leakage                 | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$                         |      | 0.2   | ±100 | nA   |
| On Charact          | eristics <sup>(2)</sup>           |                                                                           | •    |       |      |      |
| V <sub>GS(th)</sub> | Gate Threshold Voltage            | $V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$                                | 1.00 | 1.76  | 2.50 | V    |
|                     | Static Drain-Source On-Resistance | $V_{GS} = 5 \text{ V}, I_D = 0.05 \text{ A}$                              |      | 1.6   | 7.5  | Ω    |
| R <sub>DS(ON)</sub> |                                   | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.5 A                            |      |       | 2.0  |      |
|                     |                                   | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.5 A,<br>T <sub>J</sub> = 125°C |      | 2.53  | 13.5 |      |
| I <sub>D(ON)</sub>  | On-State Drain Current            | V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 7.5 V                           | 1.50 | 1.43  |      | Α    |
| 9 <sub>FS</sub>     | Forward Transconductance          | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.2 A                            | 80   | 356.5 |      | mS   |
| Dynamic Cl          | haracteristics                    |                                                                           | •    |       |      |      |
| C <sub>iss</sub>    | Input Capacitance                 |                                                                           |      | 37.8  | 50   | pF   |
| C <sub>oss</sub>    | Output Capacitance                | V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,<br>f = 1.0 MHz             |      | 12.4  | 25   | pF   |
| C <sub>rss</sub>    | Reverse Transfer Capacitance      | 1 - 1.0 WH 12                                                             |      | 6.5   | 7    | pF   |
|                     | Characteristics                   |                                                                           | •    | •     |      |      |
| t <sub>D(ON)</sub>  | Turn-On Delay Time                |                                                                           |      | 5.85  | 20   | ns   |
| t <sub>D(OFF)</sub> | Turn-Off Delay Time               | $V_{GEN}$ = 10 V, R <sub>L</sub> = 150 Ω,<br>R <sub>GEN</sub> = 25 Ω      |      | 12.5  | 20   | ns   |

#### Note:

2. Short duration test pulse used to minimize self-heating effect.

# **Typical Performance Characteristics**

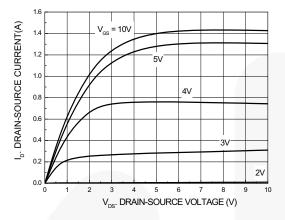


Figure 1. On-Region Characteristics

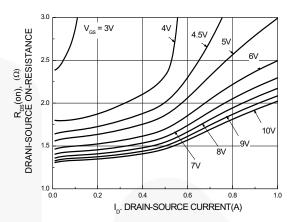


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current

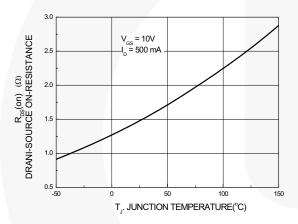


Figure 3. On-Resistance Variation with Temperature

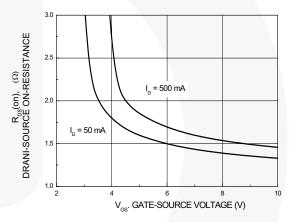


Figure 4. On-Resistance Variation with Gate-Source Voltage

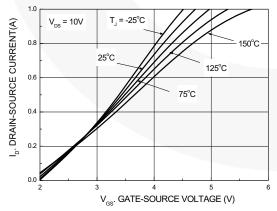


Figure 5. Transfer Characteristics

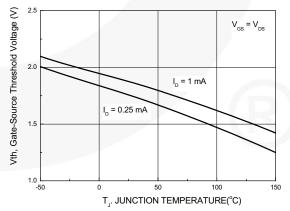


Figure 6. Gate Threshold Variation with Temperature

# **Typical Performance Characteristics** (Continued)

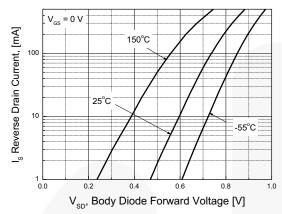


Figure 7. Reverse Drain Current Variation with Diode Forward Voltage and Temperature

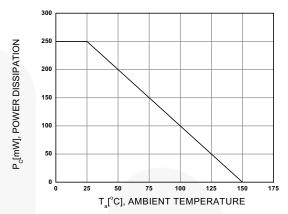


Figure 8. Power Derating

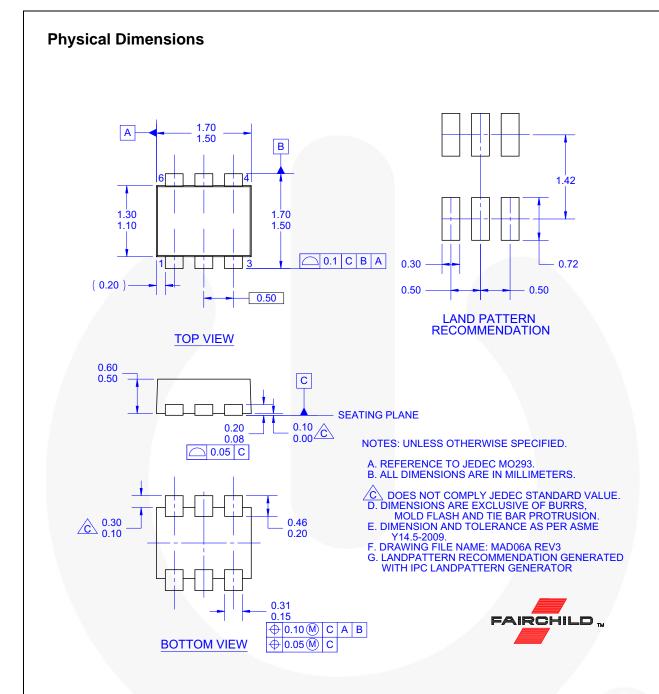


Figure 9. 6-LEAD, MO293, 1.2MM WIDE, SOT563F





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